

List of Publications by Year
in descending order

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1587
citing authors

#	ARTICLE	IF	CITATIONS
1	New Insights on the Burstein-Moss Shift and Band Gap Narrowing in Indium-Doped Zinc Oxide Thin Films. PLoS ONE, 2015, 10, e0141180.	2.5	122
2	Structural and optical properties of nanocrystalline CdS thin films prepared using microwave-assisted chemical bath deposition. Thin Solid Films, 2012, 520, 3477-3484.	1.8	97
3	Synthesis and characterization of single-crystal CdS nanosheet for high-speed photodetection. Physica E: Low-Dimensional Systems and Nanostructures, 2012, 44, 1716-1721.	2.7	67
4	High Al-content Al _x Ga _{1-x} N epilayers grown on Si substrate by plasma-assisted molecular beam epitaxy. Journal of Alloys and Compounds, 2009, 487, 24-27.	5.5	51
5	Porous GaN prepared by UV assisted electrochemical etching. Thin Solid Films, 2007, 515, 3469-3474.	1.8	48
6	Effects of oxygen percentage on the growth of copper oxide thin films by reactive radio frequency sputtering. Materials Chemistry and Physics, 2013, 140, 243-248.	4.0	47
7	Growth of CdS nanosheets and nanowires through the solvothermal method. Journal of Crystal Growth, 2012, 359, 43-48.	1.5	44
8	Growth and characterization of CdS single-crystalline micro-rod photodetector. Superlattices and Microstructures, 2013, 54, 137-145.	3.1	40
9	Growth and characterization of Zn _x Cd _{1-x} S nanoflowers by microwave-assisted chemical bath deposition. Journal of Alloys and Compounds, 2012, 541, 227-233.	5.5	38
10	Experimental and theoretical studies of surface phonon polariton of AlN thin film. Applied Physics Letters, 2007, 90, 081902.	3.3	37
11	Porous Si(111) and Si(100) as an intermediate buffer layer for nanocrystalline InN films. Journal of Alloys and Compounds, 2009, 479, L54-L58.	5.5	30
12	Surface and interface phonon polaritons of wurtzite GaN thin film grown on 6H-SiC substrate. Applied Physics Letters, 2009, 94, .	3.3	26
13	Characterizations of InN Thin Films Grown on Si (110) Substrate by Reactive Sputtering. Journal of Nanomaterials, 2011, 2011, 1-7.	2.7	26
14	Recent advances and challenges in the MOCVD growth of indium gallium nitride: A brief review. Materials Science in Semiconductor Processing, 2022, 143, 106545.	4.0	25
15	Optical properties of CdS micro/nanocrystalline structures prepared via a thermal evaporation method. Materials Science in Semiconductor Processing, 2014, 26, 87-92.	4.0	24
16	Surface phonon polariton of wurtzite GaN thin film grown on -plane sapphire substrate. Solid State Communications, 2008, 145, 535-538.	1.9	23
17	Structural Properties of Doped GaN on Si(111) Studied by X-Ray Diffraction Techniques. Journal of Nondestructive Evaluation, 2009, 28, 125-130.	2.4	23
18	Growth of GaN on sputtered GaN buffer layer via low cost and simplified sol-gel spin coating method. Vacuum, 2015, 119, 119-122.	3.5	23

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19	Synthesis of wurtzite GaN thin film via spin coating method. Materials Science in Semiconductor Processing, 2014, 17, 63-66.	4.0	22
20	Effect of hydrostatic pressure on the barrier height of Ni Schottky contacts on n-AlGaIn. Applied Physics Letters, 2006, 88, 022109.	3.3	21
21	Surface phonon polariton mode of wurtzite structure $\text{Al}_x\text{Ga}_{1-x}\text{N}$ thin films. Applied Physics Letters, 2007, 91, .	3.3	21
22	Effect of Al mole fraction on structural and electrical properties of $\text{Al}_x\text{Ga}_{1-x}\text{N}/\text{GaN}$ heterostructures grown by plasma-assisted molecular beam epitaxy. Applied Surface Science, 2011, 257, 4159-4164.	6.1	21
23	Synthesis of two-dimensional gallium nitride via spin coating method: influences of nitridation temperatures. Journal of Sol-Gel Science and Technology, 2013, 68, 95-101.	2.4	17
24	Surface phonon polariton characteristic of honeycomb nanoporous GaN thin films. Applied Physics Letters, 2013, 102, 101601.	3.3	17
25	High carrier concentrations of n- and p-doped GaN on Si(111) by nitrogen plasma-assisted molecular-beam epitaxy. Journal of Materials Research, 2007, 22, 2623-2630.	2.6	15
26	Fabrication of InN based photodetector using porous silicon buffer layer. Surface Engineering, 2013, 29, 772-777.	2.2	15
27	Structural and optical properties of In-doped ZnO thin films under wet annealing. Materials Letters, 2014, 116, 396-398.	2.6	14
28	Fabrication of titanium dioxide nanotubes in fluoride-free electrolyte via rapid breakdown anodization. Journal of Porous Materials, 2015, 22, 1437-1444.	2.6	14
29	Growth mechanism of indium nitride via sol-gel spin coating method and nitridation process. Surface and Coatings Technology, 2017, 310, 38-42.	4.8	14
30	Strong coupling of sapphire surface polariton with aluminum nitride film phonon. Physics Letters, Section A: General, Atomic and Solid State Physics, 2009, 373, 2382-2384.	2.1	13
31	Effect of annealing temperature on IR-detectors based on InN nanostructures. Vacuum, 2014, 106, 46-48.	3.5	13
32	Studies of surface and interface phonon polariton characteristics of wurtzite ZnO thin film on wurtzite 6H-SiC substrate by p-polarized infrared attenuated total reflection spectroscopy. Thin Solid Films, 2011, 519, 3703-3708.	1.8	12
33	Fabrication of porous ZnO via electrochemical etching using 10wt% potassium hydroxide solution. Materials Science in Semiconductor Processing, 2013, 16, 70-76.	4.0	12
34	Photoluminescence spectra of nitrogen-rich InN thin films grown on Si(110) and photoelectrochemical etched Si(110). Vacuum, 2014, 101, 217-220.	3.5	12
35	Comparative study on structural and optical properties of nitrogen rich InN on Si(110) and 6H-SiC. Surface Engineering, 2013, 29, 561-565.	2.2	11
36	Crystal orientation dependence of polarized infrared reflectance response of hexagonal sapphire crystal. Optical Materials, 2014, 37, 773-779.	3.6	11

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37	Far Infrared Optical Properties of Bulk Wurtzite Zinc Oxide Semiconductor. Journal of Materials Science and Technology, 2011, 27, 465-470.	10.7	10
38	Solvothermal growth of single-crystal CdS nanowires. Bulletin of Materials Science, 2014, 37, 337-345.	1.7	10
39	Dispersion of Surface and Interface Phonon Polariton Modes in Wurtzite Based Multilayer System. Journal of the Physical Society of Japan, 2011, 80, 084712.	1.6	9
40	InN PHOTOCONDUCTORS ON DIFFERENT ORIENTATIONS OF Si SUBSTRATES. International Journal of Modern Physics B, 2012, 26, 1250137.	2.0	9
41	Influence of post-annealing condition on the properties of ZnO films. Ceramics International, 2013, 39, S263-S267.	4.8	9
42	STRUCTURE AND OPTICAL PROPERTIES OF InN THIN FILM GROWN ON SiC BY REACTIVE RF MAGNETRON SPUTTERING. Surface Review and Letters, 2013, 20, 1350008.	1.1	9
43	Ultraviolet photoresponse properties of zinc oxide on type IIb diamond heterojunction. Physica B: Condensed Matter, 2010, 405, 4123-4127.	2.7	8
44	Surface and interface phonon polariton characteristics of wurtzite ZnO/GaN heterostructure. Applied Physics Letters, 2011, 98, 241909.	3.3	8
45	Theoretical studies of surface phonon polariton in wurtzite AlIn ternary alloy. Thin Solid Films, 2011, 519, 5481-5485.	1.8	8
46	Structural, optical and electrical properties of europium picrate tetraethylene glycol complex as emissive material for OLED. Journal of Luminescence, 2012, 132, 91-99.	3.1	8
47	Growth of InN thin films on different Si substrates at ambient temperature. Microelectronics International, 2013, 30, 63-67.	0.6	8
48	Effects of nitridation durations on the synthesis of wurtzite GaN thin films by spin coating method. Journal of Sol-Gel Science and Technology, 2014, 71, 329-332.	2.4	8
49	Effect of deposition conditions on properties of nitrogen rich-InN nanostructures grown on anisotropic Si (110). Materials Science in Semiconductor Processing, 2015, 35, 216-221.	4.0	8
50	Crystallinity studies of GaN/Si films grown at different temperatures by infrared reflectance spectroscopy. Materials Chemistry and Physics, 2005, 91, 404-408.	4.0	7
51	Ohmic-Rectifying Conversion of Ni Contacts on ZnO and the Possible Determination of ZnO Thin Film Surface Polarity. PLoS ONE, 2014, 9, e86544.	2.5	7
52	Determination of Acceptor Concentration, Depletion Width, Donor Level Movement and Sensitivity Factor of ZnO on Diamond Heterojunction under UV Illumination. PLoS ONE, 2014, 9, e89348.	2.5	7
53	Surface phonon polariton responses of hexagonal sapphire crystals with non-polar and semi-polar crystallographic planes. Optics Letters, 2014, 39, 5467.	3.3	7
54	Luminescence evolution of porous GaN thin films prepared via UV-assisted electrochemical etching. Journal of Luminescence, 2015, 159, 303-311.	3.1	7

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55	Sol-gel spin coating growth of magnesium-doped indium nitride thin films. Vacuum, 2018, 155, 16-22.	3.5	7
56	Composition Dependence of Surface Phonon Polariton Mode in Wurtzite In _x Ga _{1-x} N (0 ≤ x ≤ 1) Ternary Alloy. Chinese Physics Letters, 2008, 25, 4378-4380.	3.3	6
57	SURFACE PHONON-POLARITON MODES OF WURTZITE STRUCTURE InN SEMI-INFINITE CRYSTAL. Surface Review and Letters, 2009, 16, 355-358.	1.1	6
58	Sapphire surface polariton splitting due to resonance with aluminum nitride film phonon. Journal of Physics: Conference Series, 2010, 210, 012027.	0.4	6
59	Surface phonon polariton characteristics of bulk wurtzite ZnO crystal. Physica B: Condensed Matter, 2011, 406, 115-118.	2.7	6
60	Optical properties of photo-electrochemical etching of anisotropic silicon (110). IEICE Electronics Express, 2012, 9, 752-757.	0.8	6
61	Synthesis of nanocrystalline In ₂ O ₃ on different Si substrates at wet oxidation environment. Optik, 2013, 124, 2679-2681.	2.9	6
62	Optical and structural properties of porous zinc oxide fabricated via electrochemical etching method. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2013, 178, 956-959.	3.5	6
63	Effects of Nitridation Temperature on Characteristics of Gallium Nitride Thin Films Prepared Via Two-Step Method. Acta Metallurgica Sinica (English Letters), 2015, 28, 362-366.	2.9	6
64	The dependence of indium incorporation on specified temperatures in growing InGaN/GaN heterostructure using MOCVD technique. Materials Research Bulletin, 2021, 137, 111176.	5.2	6
65	The Effects of Thermal Treatments on Microstructure Phosphorus-Doped ZnO Layers Grown by Thermal Evaporation. Composite Interfaces, 2010, 17, 863-872.	2.3	5
66	Polarized infrared reflectance studies for wurtzite InN epilayers on Si(111) grown by molecular beam epitaxy. Thin Solid Films, 2011, 520, 739-742.	1.8	5
67	Experimental investigation of long-wavelength optical lattice vibrations in quaternary Al _x In _y Ga _{1-x-y} N alloys and comparison with results from the pseudo-unit cell model. Physica B: Condensed Matter, 2011, 406, 1379-1384.	2.7	5
68	EFFECT OF CURRENT DENSITY ON OPTICAL PROPERTIES OF ANISOTROPIC PHOTOELECTROCHEMICAL ETCHED SILICON (110). Modern Physics Letters B, 2012, 26, 1250131.	1.9	5
69	Surface phonon polariton of wurtzite AlN thin film grown on sapphire. Materials Chemistry and Physics, 2012, 134, 493-498.	4.0	5
70	Calculation of dispersion of surface and interface phonon polariton resonances in wurtzite semiconductor multilayer system taking damping effects into account. Thin Solid Films, 2014, 551, 114-119.	1.8	5
71	Influence of initial sulfur content in precursor solution for the growth of molybdenum disulfide. Journal of Physics: Conference Series, 2018, 995, 012060.	0.4	5
72	Sol-gel-derived gallium nitride thin films for ultraviolet photodetection. Microelectronics International, 2019, 36, 8-13.	0.6	5

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73	Polarized infrared reflectance study of wurtzite GaN thin film: The effects of angle of incidence on the optical phonon modes. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2007, 25, 1557-1561.	2.1	4
74	Effect of zinc on the growth mechanism of zinc oxide nanostructures in the nitrogen environment. Journal Physics D: Applied Physics, 2008, 41, 055506.	2.8	4
75	Surface phonon polariton characteristics of In _{0.04} Al _{0.06} Ga _{0.90} N/AlN/Al ₂ O ₃ heterostructure. Optics Express, 2010, 18, 10354.	3.4	4
76	Substrate surface polariton splitting due to thin zinc oxide and aluminum nitride films presence. Applied Surface Science, 2013, 267, 93-96.	6.1	4
77	Polarized infrared reflectance study of free standing cubic GaN grown by molecular beam epitaxy. Materials Chemistry and Physics, 2014, 146, 121-128.	4.0	4
78	Influences of elevated thermal decomposition of ammonia gas on indium nitride grown by sol-gel spin coating method. Materials Research Bulletin, 2017, 96, 258-261.	5.2	4
79	Photostrictive behavior as the piezo-phototronic effect in InGaN/GaN multiple quantum wells. Nano Energy, 2021, 86, 106085.	16.0	4
80	The Study of Energy Band Gap of In _x Al _y Ga _{1-x-y} N Quaternary Alloys using UV-VIS Spectroscopy. , 2009, , .		3
81	Characterization of Al _x In _y Ga _{1-x-y} N quaternary alloys grown on sapphire substrates by molecular-beam epitaxy. Materials Science in Semiconductor Processing, 2011, 14, 164-169.	4.0	3
82	Fabrication of porous ZnO thin films using wet chemical etching with 0.5% HNO ₃ . Microelectronics International, 2012, 29, 96-100.	0.6	3
83	Infrared reflectance studies of hillock-like porous zinc oxide thin films. Thin Solid Films, 2013, 539, 70-74.	1.8	3
84	Characterizations of Nitrogen Doped Cupric Oxide Thin Films Deposited on Different Substrates for Solar Cell Applications. Advanced Materials Research, 0, 925, 469-473.	0.3	3
85	Preparation and characterization of Zn _x Cd _{1-x} S ternary alloys micro/nanostructures grown by thermal evaporation. Materials Research Express, 2015, 2, 016501.	1.6	3
86	Growth and Characterization of AlN Thin Film Deposited by Sol-Gel Spin Coating Techniques. Advanced Materials Research, 2015, 1107, 667-671.	0.3	3
87	Reactive Sputtering Growth of Indium Nitride Thin Films on Flexible Substrate Under Different Substrate Temperatures. Journal of Physics: Conference Series, 2020, 1535, 012029.	0.4	3
88	Multiple electromagnetically induced transparency-like effects of a metal nanostructure induced by a graphene grating deposited on a gallium oxide substrate. Applied Optics, 2020, 59, 7918.	1.8	3
89	Analysis using a two-layer model of the transport properties of InGaN epilayers grown on GaN template substrate. Materials Science in Semiconductor Processing, 2022, 144, 106614.	4.0	3
90	p-polarized infrared attenuated total reflection study of InN thin films grown on Si(111) substrate. Physica Status Solidi - Rapid Research Letters, 2010, 4, 191-193.	2.4	2

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91	Kramers-Kronig Analysis of Infrared Reflectance Spectra for Quaternary $\text{In}_{1-x}\text{Al}_x\text{Ga}_{1-y}\text{N}$ Alloy. AIP Conference Proceedings, 2010, , .	0.4	2
92	Surface phonon polariton characteristics of wurtzite ZnO thin film grown on silicon substrate. Physica Status Solidi (B): Basic Research, 2012, 249, 1058-1062.	1.5	2
93	Insights on semiconductor-metal transition in indium-doped zinc oxide from x-ray photoelectron spectroscopy, time-of-flight secondary ion mass spectrometry and x-ray diffraction. AIP Conference Proceedings, 2016, , .	0.4	2
94	Radio-Frequency Sputtering Growth of Indium Nitride Thin Film on Flexible Substrate. Materials Science Forum, 0, 846, 650-656.	0.3	2
95	Effects of coating cycles on spin-coated indium nitride thin films. Surface Engineering, 2018, 34, 554-561.	2.2	2
96	Infrared reflectance characterization of porous GaN thin films on sapphire substrate using factorized-Rayleigh model. Optical Materials, 2019, 96, 109320.	3.6	2
97	Growth process of molybdenum disulfide thin films grown by thermal vapour sulfurization. Journal of Materials Science: Materials in Electronics, 2019, 30, 10419-10426.	2.2	2
98	UV Photodetector Based on Mg-Doped GaN Thin Films Prepared by Sol-Gel Spin Coating. Solid State Phenomena, 2019, 290, 208-213.	0.3	2
99	Aluminum Nitride Thin Films Grown by Sol-Gel Spin Coating Technique. Solid State Phenomena, 0, 290, 137-141.	0.3	2
100	Growth Temperature Dependence of Sol-Gel Spin Coated Indium Nitride Thin Films. Solid State Phenomena, 0, 290, 153-159.	0.3	2
101	Effect of pH on the Synthesis of Cobalt Selenide Films by SILAR Method. Oriental Journal of Chemistry, 2021, 37, 791-796.	0.3	2
102	Development of Novel Thin Film Solar Cells: Design and Numerical Optimisation. Journal of Physical Science, 2019, 30, 199-205.	0.9	2
103	AlGa _N metal-semiconductor-metal structure for pressure sensing applications. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 2287-2290.	0.8	1
104	The Energy Band Gap of $\text{Al}_x\text{Ga}_{1-x}\text{N}$ Thin Films as a Function of Al-Mole Fraction. , 2006, , .		1
105	Determination of the Al Composition of $\text{Al}_x\text{Ga}_{1-x}\text{N}$ Thin Films By Means Of EDX and XRD Techniques. , 2010, , .		1
106	Structural and optical properties of $\text{Al}_x\text{In}_y\text{Ga}_{1-x-y}\text{N}$ quaternary alloys grown on sapphire substrates by molecular beam epitaxy. Microelectronics International, 2010, 27, 148-153.	0.8	1
107	The Study of Energy Band Gap of $\text{Al}_x\text{In}_y\text{Ga}_{1-x-y}\text{N}$ Quaternary Alloys Using UV-VIS Spectroscopy. , 2010, , .		1
108	Photoluminescence and XRD Crystalline Studies of $\text{In}_x\text{Al}_y\text{Ga}_{1-x-y}\text{N}$ Quaternary Alloys. IOP Conference Series: Materials Science and Engineering, 2011, 17, 012006.	0.6	1

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109	Strong Room Temperature 505 nm Emission from Hexagonal Crack Free InGaN Thin Film on Si(111) Grown by MBE. Composite Interfaces, 2011, 18, 37-47.	2.3	1
110	X-ray diffraction studies of Al _x Ga _{1-x} N (0 ≤ x ≤ 1) ternary alloys grown on sapphire substrate. Microelectronics International, 2011, 28, 44-48.	0.6	1
111	A Simple Method to Prepare Indium Oxide Nanoparticles on Si (110). Advanced Materials Research, 0, 620, 193-197.	0.3	1
112	Surface and optical phonon characteristics of ZnO/diamond heterostructure. Ceramics International, 2013, 39, S529-S532.	4.8	1
113	Polarized infrared reflectance characterization of wurtzite ZnO/GaN heterostructure on 6H-SiC substrate. , 2013, , .		1
114	Ultraviolet Photoresponse Properties of Zinc Oxide Nanorods on Heavily Boron-Doped Diamond Heterostructure. Advanced Materials Research, 2013, 832, 172-177.	0.3	1
115	Formation and Optical Studies of Porous GaN Thin Films via UV-Assisted Electrochemical Etching Approach. Advanced Materials Research, 2014, 895, 45-50.	0.3	1
116	Polarized infrared attenuated total reflection study of sapphire crystals with different crystallographic planes. AIP Conference Proceedings, 2015, , .	0.4	1
117	Doped indium nitride thin film by sol-gel spin coating method. AIP Conference Proceedings, 2017, , .	0.4	1
118	Low-cost growth of magnesium doped gallium nitride thin films by sol-gel spin coating method. IOP Conference Series: Materials Science and Engineering, 2018, 284, 012031.	0.6	1
119	Effects of microwave activation power on the structural properties of sol-gel spin coated magnesium doped gallium nitride thin films. Materials Today: Proceedings, 2019, 16, 1673-1679.	1.8	1
120	Reversible Circular Dichroism Induced by Energy Losses without Changing Chirality of Structure. Annalen Der Physik, 2020, 532, 1900539.	2.4	1
121	Fabrication and characterization of InN-based metal-semiconductor-metal infrared photodetectors prepared using sol-gel spin coated technique. Functional Materials Letters, 2021, 14, 2151024.	1.2	1
122	The role of growth temperature on the indium incorporation process for the MOCVD growth of InGaN/GaN heterostructures. Microelectronics International, 2021, 38, 105-112.	0.6	1
123	Sol-Gel Spin Coating Growth of Magnesium-Doped Indium Nitride Thin Films on Different Substrates. Engineering Journal, 2020, 24, 285-294.	1.0	1
124	Effects of indium composition on the surface morphological and optical properties of InGaN/GaN heterostructures. Microelectronics International, 2023, 40, 8-16.	0.6	1
125	Optical Properties of GaN on Si Substrate Using Plasma-Assisted MOCVD Technique in the Infrared and Visible Regions. Materials Science Forum, 2005, 480-481, 519-524.	0.3	0
126	Growth and Properties of GaN/Si Heterojunction. Materials Science Forum, 2005, 480-481, 531-536.	0.3	0

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127	Crystallinity Studies of GaN/Si Films Grown by MOCVD at Various Substrate Temperatures Using XRD. Materials Science Forum, 2006, 517, 69-72.	0.3	0
128	Structural Properties Studies of GaN on 6H-SiC by Means of X-Ray Diffraction Technique. Advanced Materials Research, 2010, 173, 40-43.	0.3	0
129	XRD Analyses of In _[sub 0.10] Al _[sub x] Ga _[sub 0.90-x] N (0 ≤ x ≤ 0.20) Quaternary Alloys. , 2010, , .		0
130	Polarized Infrared Reflectance Studies of Quaternary In _[sub 0.04] Al _[sub 0.06] Ga _[sub 0.90] N. , 2010, , .		0
131	Thermal Degradation of Single Crystal Zinc Oxide and the Growth of Nanostructures. , 2010, , .		0
132	Polarized Infrared Reflectance Study of InGaN Semiconductor. , 2010, , .		0
133	Photoluminescence Characterization of ZnO Thin Films Grown by RF- Sputtering. , 2011, , .		0
134	Structural Properties Studies of Zinc Oxide Thin Film Grown on Silicon Carbide by Means of X-ray Diffraction Technique. , 2011, , .		0
135	Effect of in Concentration on the Optical Lattice Vibrations in Quaternary Al _{[sub >x]/sub >In_{[sub >y]/sub >Ga_{[sub >1-x-y]/sub >N Alloys. Advanced Materials Research, 0, 501, 281-285.}}}	0.3	0
136	Reactive Sputtering Growth and Characterizations of InN Thin Films on Si Substrates. Advanced Materials Research, 2012, 545, 290-293.	0.3	0
137	Structural and morphological properties of zinc oxide thin films grown on silicon substrates. , 2013, , .		0
138	Fabrication and characterization of macroporous zinc oxide. , 2013, , .		0
139	Effects of Nitridation Temperatures on Gallium Nitride Thin Films Formed on Silicon Substrates. Advanced Materials Research, 0, 895, 57-62.	0.3	0
140	Spin Coating Deposition of <i>c</i>-Oriented Wurtzite Gallium Nitride Thin Film. Applied Mechanics and Materials, 0, 699, 70-75.	0.2	0
141	Characteristics of Cuprous Oxide Thin Films Deposited on Glass and Polyethylene Terephthalate Substrates. Advanced Materials Research, 0, 895, 29-34.	0.3	0
142	Influence of force constant on surface phonon polariton properties of cubic ZnS _{1-x} Se _x crystals. AIP Conference Proceedings, 2015, , .	0.4	0
143	Effects of sputtering power on properties of copper oxides thin films deposited on glass substrates. AIP Conference Proceedings, 2015, , .	0.4	0
144	Theoretical Studies on Optical Phonon and Surface Phonon Polariton of Wurtzite AlInN Alloys. Advanced Materials Research, 0, 1107, 565-570.	0.3	0

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145	Attenuated Total Reflection Studies of Honeycomb Nanoporous GaN Thin Films. Advanced Materials Research, 0, 1108, 9-14.	0.3	0
146	Infrared optical responses of wurtzite $\text{In}_x\text{Ga}_{1-x}\text{N}$ thin films with porous surface morphology. Thin Solid Films, 2016, 603, 334-341.	1.8	0
147	An investigation of GaN thin films on AlN on sapphire substrate by sol-gel spin coating method. AIP Conference Proceedings, 2017, , .	0.4	0
148	Synthesis of gallium nitride thin films using sol-gel dip coating method. AIP Conference Proceedings, 2017, , .	0.4	0
149	Influence of sulfurization temperature on the molybdenum disulfide thin films grown by thermal vapour sulfurization. Materials Today: Proceedings, 2019, 17, 921-928.	1.8	0
150	Comparative Study of Gas Ratio on Indium Nitride Thin Films Grown on Flexible Substrates Prepared by Reactive Sputtering Method. Solid State Phenomena, 2019, 290, 142-146.	0.3	0
151	A systematic study on the growth of molybdenum disulfide with the carbon disulfide as the sulfurizing source. Ceramics International, 2019, 45, 13701-13710.	4.8	0
152	Influence of the substrate types on the molybdenum disulfide grown by thermal vapour sulfurization. Superlattices and Microstructures, 2019, 129, 69-76.	3.1	0
153	Anisotropy of DNA molecule detection and enhancement by GaN-based electronic sensor. Optics Letters, 2022, 47, 417.	3.3	0
154	Characterization and tuning of anisotropy property of grating structure using electrical method. Optik, 2022, 262, 169338.	2.9	0
155	Electrostatic Contribution to the Photo-Assisted Piezoresponse Force Microscopy by Photo-Induced Surface Charge. Microscopy and Microanalysis, 0, , 1-5.	0.4	0